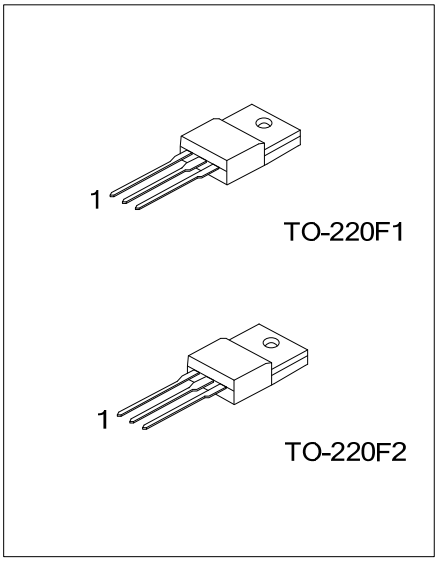
30A, 150V N-CHANNEL POWER MOSFET



■ DESCRIPTION

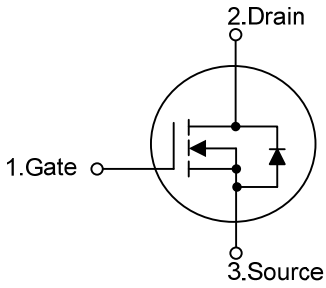
The UTC **30N15-HC** is a N-channel enhancement MOSFET using UTC's advanced technology to provide the customers with perfect $R_{DS(ON)}$, high switching speed, high current capacity and low gate charge.

The UTC **30N15-HC** is universally applied in low voltage such as automotive, high efficiency switching for AC/DC converters and DC motor control, etc.

■ FEATURES

* $R_{DS(ON)} \leq 80\ m\Omega$ @ V_{GS}=10V, I_D=15A
* High Switching Speed

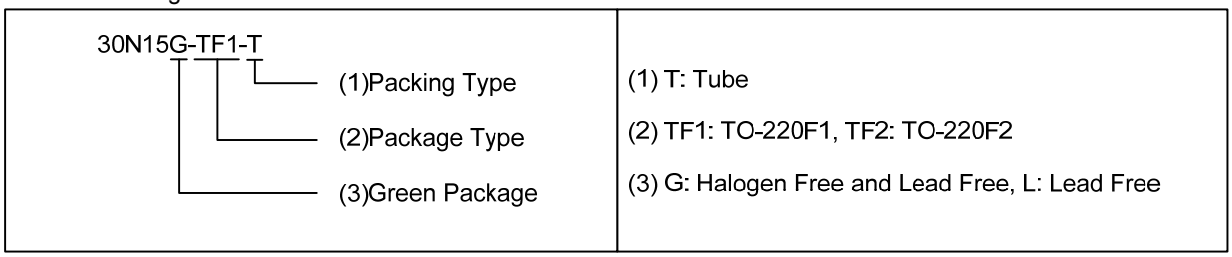
■ SYMBOL



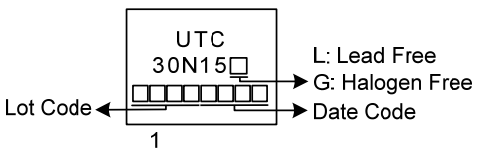
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
30N15L-TF1-T	30N15G-TF1-T	TO-220F1	G	D	S	Tube
30N15L-TF2-T	30N15G-TF2-T	TO-220F2	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source



■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	150	V
Gate-Source Voltage		V_{GSS}	±30	V
Continuous Drain Current	Continuous	I_D	30	A
	Pulsed	I_{DM}	60	A
Single Pulsed Avalanche Current		I_{AS}	29.8	A
Single Pulsed Avalanche Energy		E_{AS}	89.1	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	3.4	V/ns
Power Dissipation		P_D	42.5	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating : Pulse width limited by maximum junction temperature.
3. L=0.1mH, I_{AS}=29.8A, V_{DD}=50V, R_G=25Ω, Starting T_J = 25°C
4. I_{SD}≤30A, di/dt≤200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ_{JA}	62.5	°C/W
Junction to Case	θ_{JC}	2.9	°C/W

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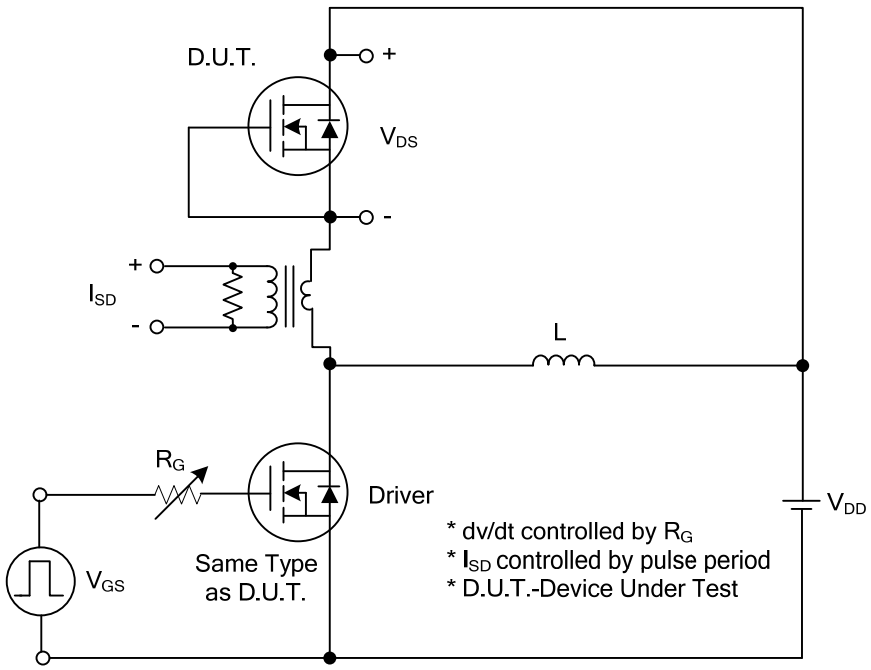
■ ELECTRICAL CHARACTERISTICS

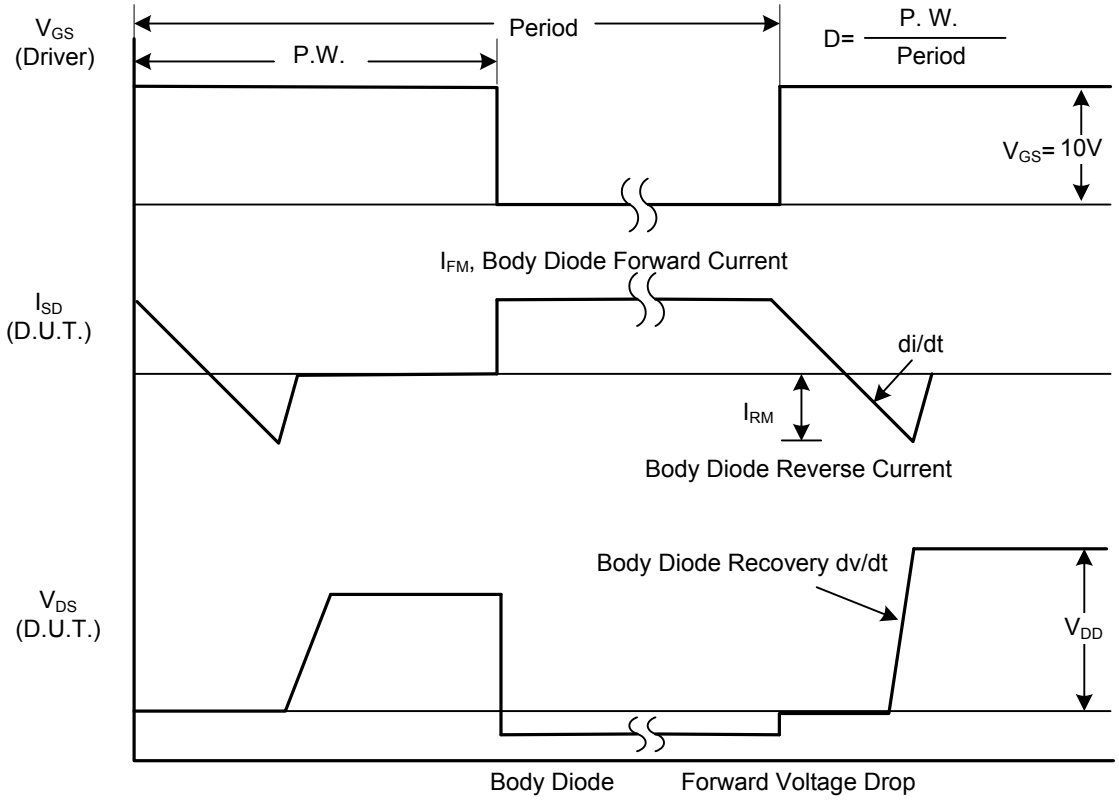
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D=250μA, V_{GS}=0V	150			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=150V, V_{GS}=0V			10	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS}=+30V, V_{DS}=0V			+100	nA
	Reverse		V_{GS}=-30V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=15A			80	mΩ
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		993.4		pF
Output Capacitance		C_{OSS}			214.7		pF
Reverse Transfer Capacitance		C_{RSS}			13.5		pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_G	V_{DS}=120V, V_{GS}=10V, I_D=30A I_G=1mA (Note 1, 2)		28.7		nC
Gate to Source Charge		Q_{GS}			11.4		nC
Gate to Drain Charge		Q_{GD}			7.4		nC
Turn-ON Delay Time		$t_{D(ON)}$	V_{DD}=100V, V_{GS}=10V, I_D=30A, R_G=6.0Ω (Note 1, 2)		7.6		ns
Rise Time		t_R			16.8		ns
Turn-OFF Delay Time		$t_{D(OFF)}$			18.1		ns
Fall-Time		t_F			17.2		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S				30	A
Maximum Body-Diode Pulsed Current		I_{SM}				60	A
Drain-Source Diode Forward Voltage		V_{SD}	I_S=30A, V_{GS}=0V			1.4	V
Body Diode Reverse Recovery Time		t_{rr}	I_S=30A, V_{GS}=0V, dI_F/dt=100A/μs (Note 1)		98.6		ns
Reverse Recovery Charge		Q_{rr}			0.7		μC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

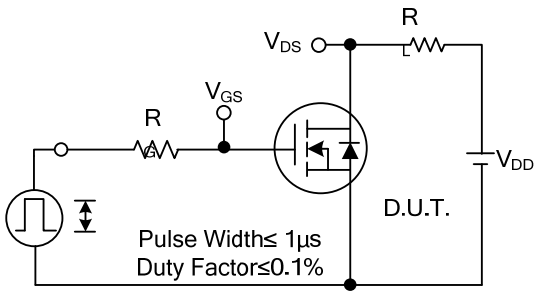


Peak Diode Recovery dv/dt Test Circuit

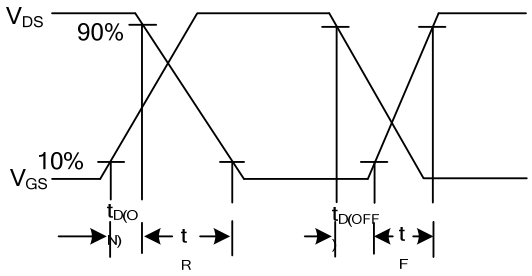


Peak Diode Recovery dv/dt Waveforms

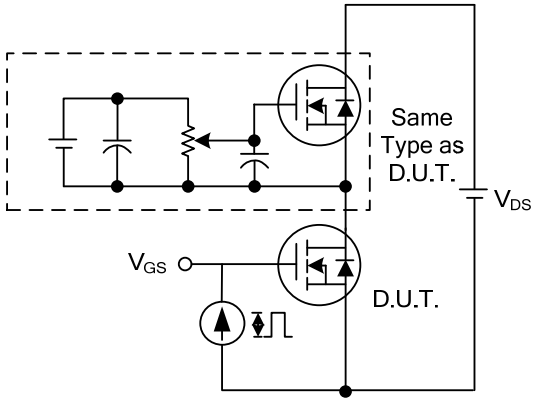
■ TEST CIRCUITS AND WAVEFORMS



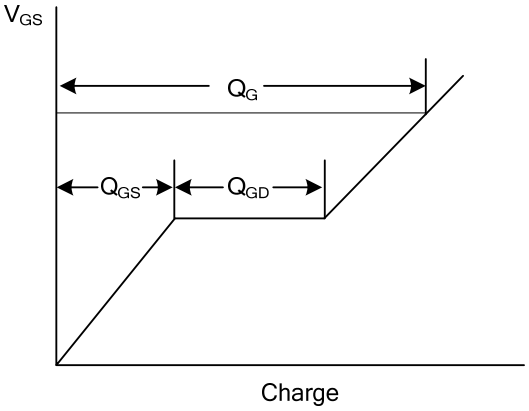
Switching Test Circuit



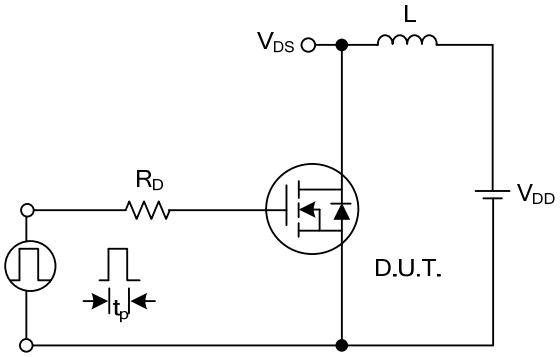
Switching Waveforms



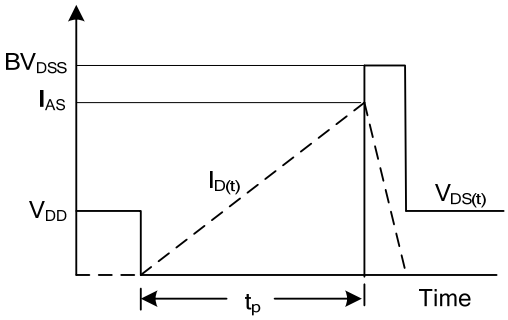
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms